Low-leakage switching diode 188380

Applications

Low leakage switching

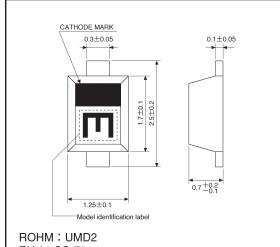
Features

- 1) High reliability.
- 2) Small surface mounting type. (UMD2)
- 3) The typical reverse current is extremely low of 40pA.

Construction

Silicon epitaxial planar

External dimensions (Units: mm)



EIAJ: SC-76 JEDEC: SOD-323

Absolute maximum ratings

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	VR	35	V
Peak forward current	Іғм	225	mA
Mean rectifying current	lo	100	mA
Surge current (1 μs)	Isurge	400	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	−55∼ +125	°C

Electrical characteristics

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditons
Forward voltage	VF	_	0.94	1.2	V	I _F =100mA
Reverse current	IR	_	0.04	10	nA	V _R =20V
Capacitance between terminals	Ст	_	2.8	5.0	pF	V _R =0.5V, f=1MHz

Diodes 1SS380

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

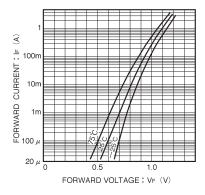


Fig. 1 Forward characteristics

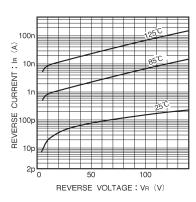


Fig. 2 Reverse characteristics

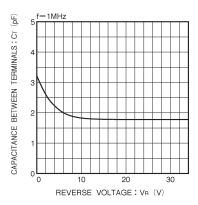


Fig. 3 Capacitance between terminals characteristics

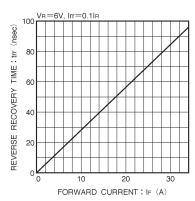


Fig. 4 Reverse recovery time characteristics

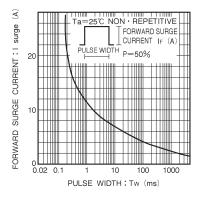


Fig. 5 Surge current characteristics

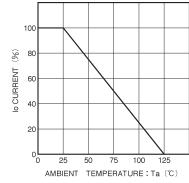


Fig. 6 Derating curve (mounting on glass epoxy PCBs)